

**SANYO**

No.4232

**2SJ256**

P-Channel MOS Silicon FET

Very High-Speed  
Switching Applications**Features**

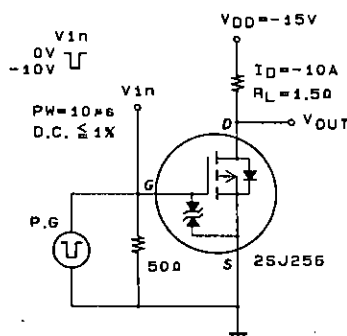
- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Micaless package facilitating mounting.

**Absolute Maximum Ratings at Ta = 25°C**

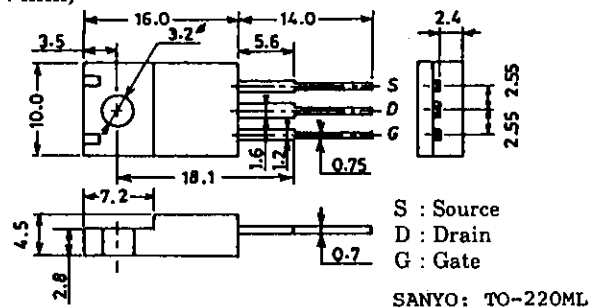
			unit
Drain to Source Voltage	$V_{DSS}$	-30	V
Gate to Source Voltage	$V_{GSS}$	$\pm 15$	V
Drain Current(DC)	$I_D$	-18	A
Drain Current(Pulse)	$I_{DP}$	$PW \leq 10\mu s, \text{ duty cycle} \leq 1\%$	-72 A
Allowable Power Dissipation	$P_D$	2.0	W
		$T_c = 25^\circ C$	30 W
Channel Temperature	$T_{ch}$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ C$

**Electrical Characteristics at Ta = 25°C**

			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1mA, V_{GS} = 0$	-30			V
G-S Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 100\mu A, V_{DS} = 0$	$\pm 15$			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -30V, V_{GS} = 0$			-100	$\mu A$
Gate to Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 12V, V_{DS} = 0$			$\pm 10$	$\mu A$
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10V, I_D = -1mA$	-1.0		-2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10V, I_D = -10A$	8.5	14		S
Static Drain to Source on State Resistance	$R_{DS(on)}$	$I_D = -10A, V_{GS} = -10V$		40	55	$m\Omega$
	$R_{DS(on)}$	$I_D = -10A, V_{GS} = -4V$		55	75	$m\Omega$
Input Capacitance	$C_{iss}$	$V_{DS} = -10V, f = 1MHz$		2000		pF
Output Capacitance	$C_{oss}$	$V_{DS} = -10V, f = 1MHz$		1200		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS} = -10V, f = 1MHz$		440		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		18		ns
Rise Time	$t_r$	"		50		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		400		ns
Fall Time	$t_f$	"		400		ns
Diode Forward Voltage	$V_{SD}$	$I_S = -18A, V_{GS} = 0$	-1.0	-1.5		V

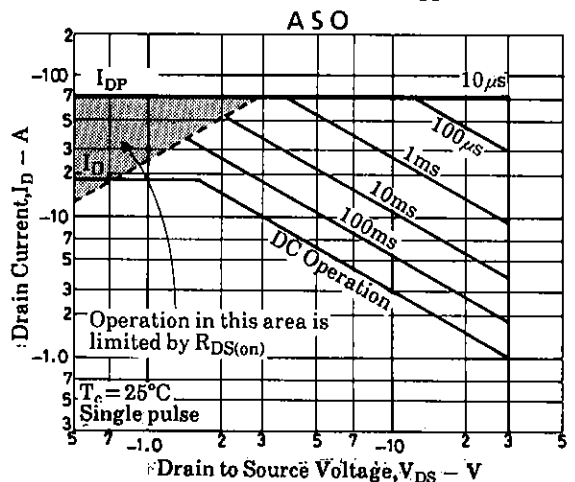
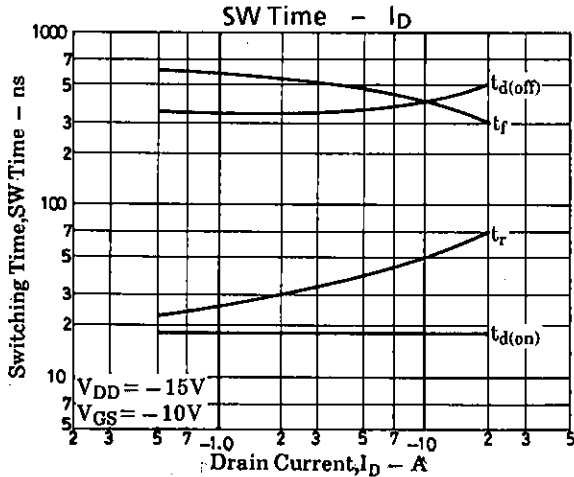
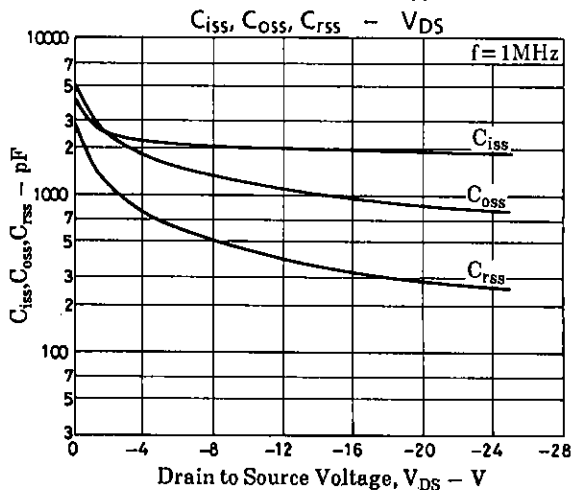
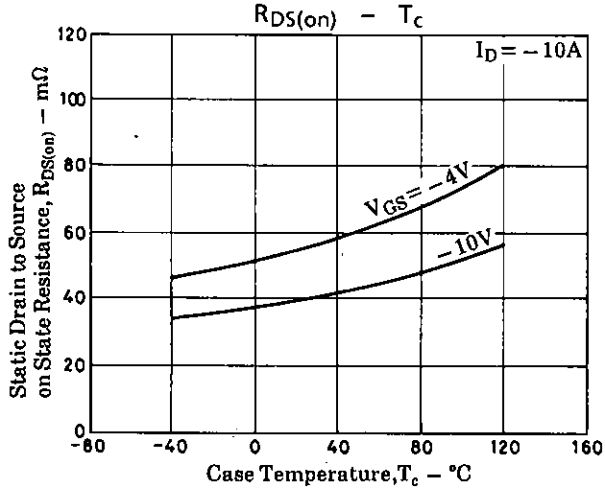
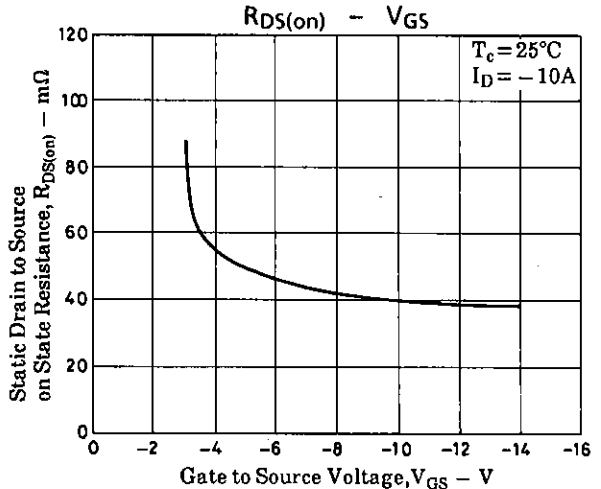
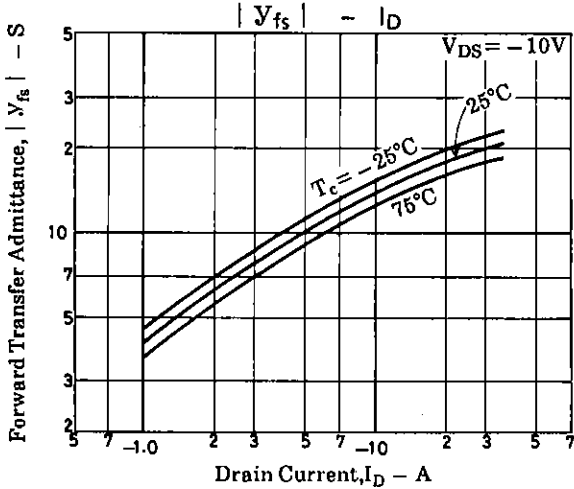
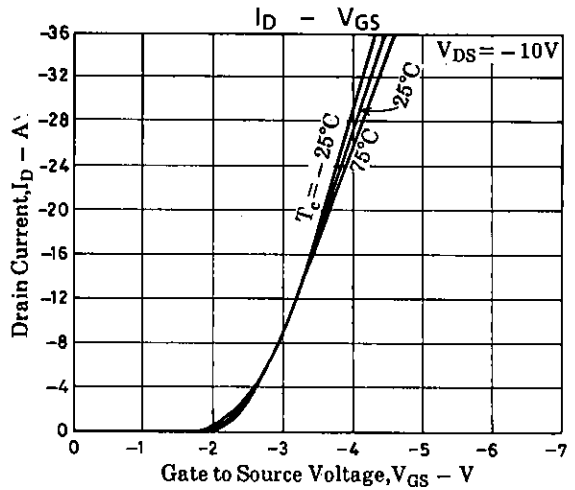
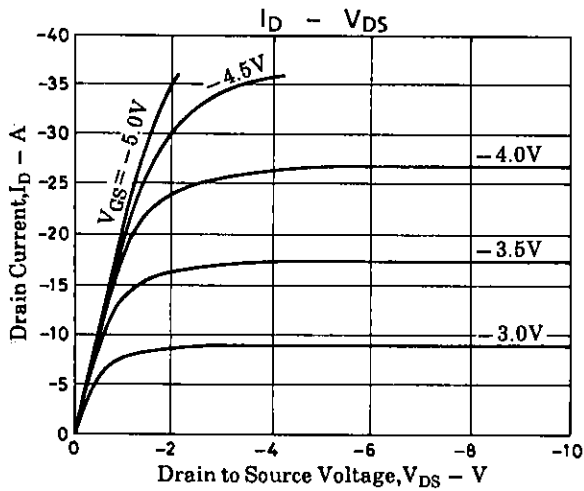
**Switching Time Test Circuit****Package Dimensions 2063**

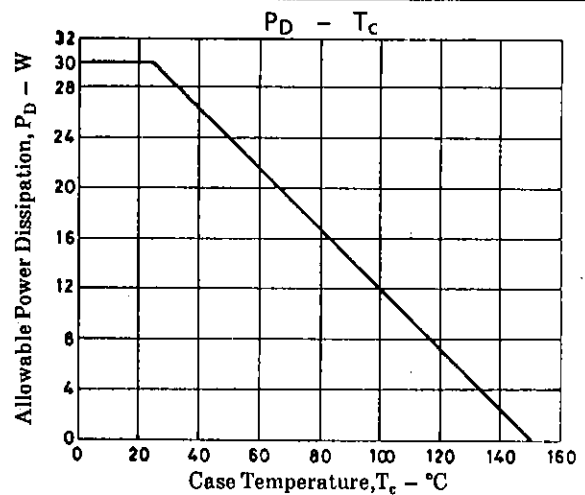
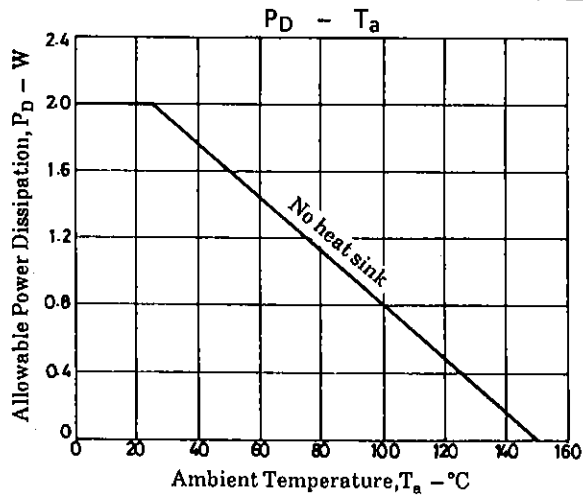
(unit : mm)



**SANYO Electric Co., Ltd. Semiconductor Business Headquarters**  
TOKYO OFFICE Tokyo Bldg. 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

42893TH (KOTO) AX-8376 No.4232-1/3





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